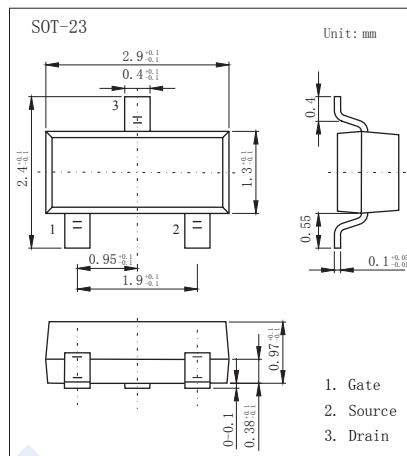
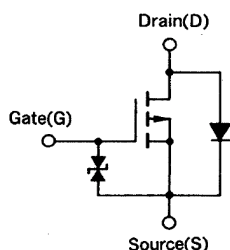


P-Channel MOSFET

2SJ204

■ Features

- $V_{DS} (V) \approx -30V$
- $I_D \approx -200mA$
- $R_{DS(ON)} < 8\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 13\Omega$ ($V_{GS} = -4V$)
- Complementary to 2SK1582



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-200	mA
Pulsed Drain Current (Note.1)	I_{DM}	-400	
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	$^\circ C$
Operating Temperature	T_{opt}	-55 to 80	
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10ms$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{BSS}	$I_D = -250\mu A$, $V_{GS} = 0V$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V$, $V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 20V$			± 1	μA
Gate Cut off Voltage	$V_{GS(off)}$	$V_{DS} = -5V$, $I_D = -1\mu A$	-1.4		-2.4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4V$, $I_D = -10mA$			13	Ω
		$V_{GS} = -10V$, $I_D = -10mA$			8	
Forward Transconductance	g_{FS}	$V_{DS} = -5V$, $I_D = -10mA$	20			mS
Input Capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = -10V$, $f = 1MHz$		27		pF
Output Capacitance	C_{oss}			27		
Reverse Transfer Capacitance	C_{rss}			6		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = -4V$, $V_{DS} = -5V$, $I_D = -0.3A$, $R_L = 1.5\Omega$, $R_{GEN} = 10\Omega$		120		ns
Turn-On Rise Time	t_r			240		
Turn-Off DelayTime	$t_{d(off)}$			135		
Turn-Off Fall Time	t_f			210		

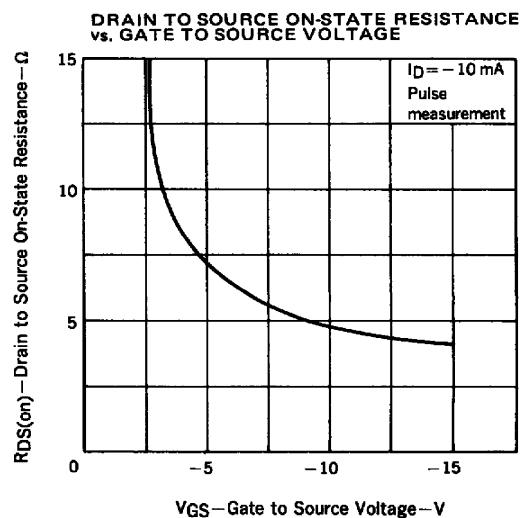
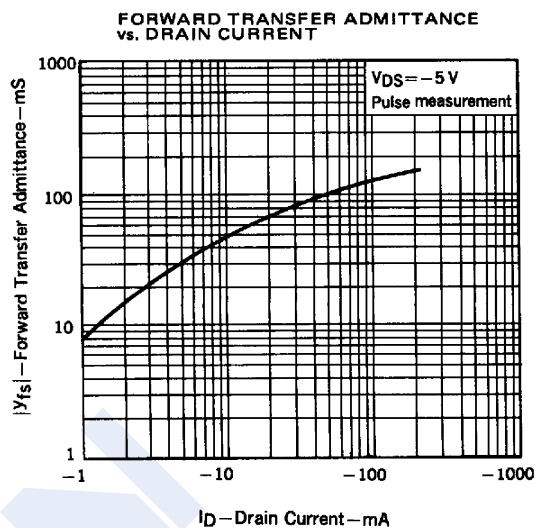
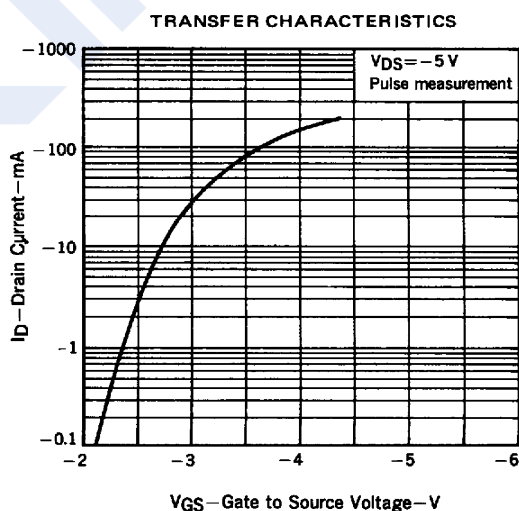
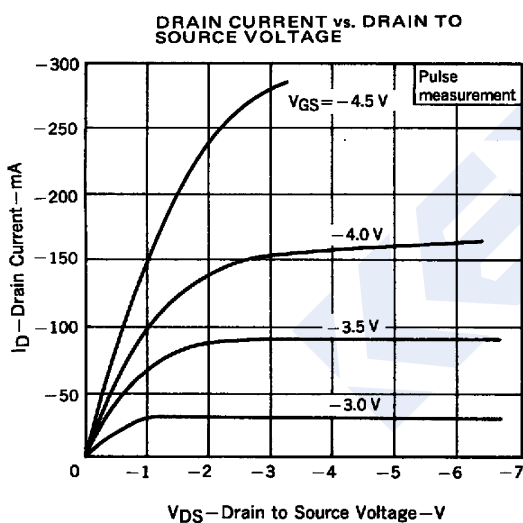
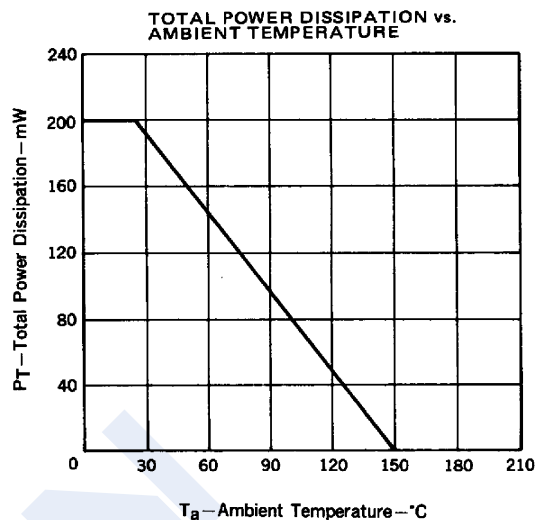
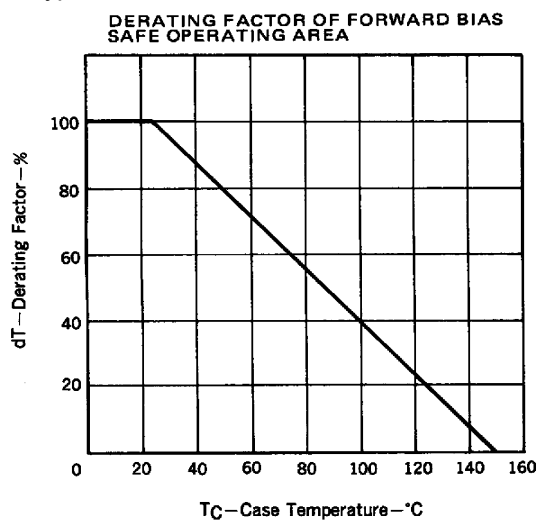
■ Marking

Marking	H15
---------	-----

P-Channel MOSFET

2SJ204

■ Typical Characteristics



P-Channel MOSFET

2SJ204

■ Typical Characteristics

